# 2SD2242, 2SD2242A

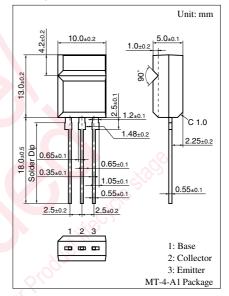
## Silicon NPN triple diffusion planar type Darlington

For power amplification

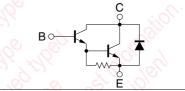
#### Features

- $\bullet$  High forward current transfer ratio  $h_{FE}$
- High-speed switching
- Allowing supply with the radial taping
- Absolute Maximum Ratings  $T_C = 25^{\circ}C$

Symbol	Rating	Unit
2242 V <sub>CBO</sub>	60	v
2242A	80	
2242 V <sub>CEO</sub>	60	v
2242A	80	
V <sub>EBO</sub>	5	v
I <sub>CP</sub>	8	А
I <sub>C</sub>	4	А
= 25°C P <sub>C</sub>	15	W
25°C	2	
Tj	150	°C
T <sub>stg</sub>	-55 to +150	°C
	$\begin{array}{c c} 2242 \\ 2242 \\ 2242A \\ \hline V_{CBO} \\ 2242A \\ \hline V_{CEO} \\ \hline 2242A \\ \hline V_{EBO} \\ \hline I_{CP} \\ I_{C} \\ \hline I_{C} \\ \hline 25^{\circ}C \\ \hline T_{j} \\ \hline \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $



#### Internal Connection



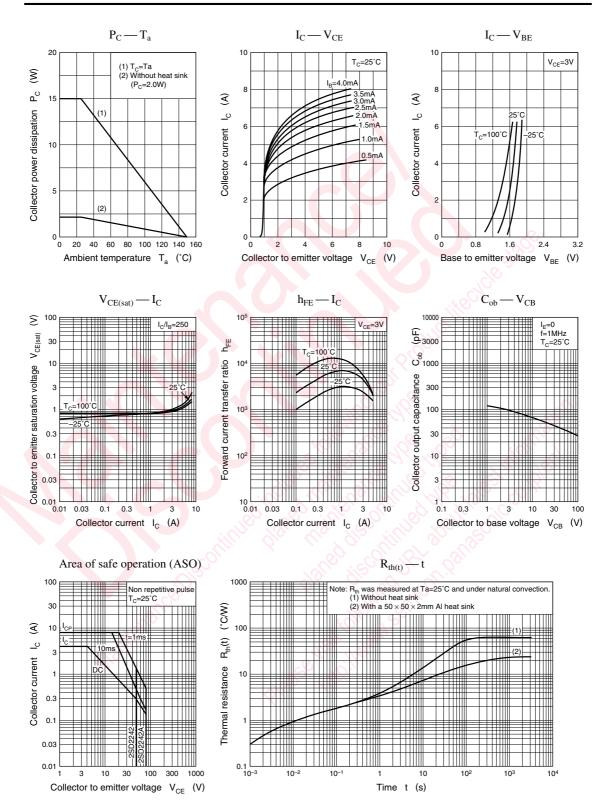
### Electrical Characteristics $T_c = 25^{\circ}C$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff	2SD2242	I <sub>CBO</sub>	$V_{CB} = 60 \text{ V}, I_E = 0$	-05	- Clip	200	μΑ
current	2SD2242A	and the second s	$V_{CB} = 80 \text{ V}, I_E = 0$	20	5	200	
Collector cutoff	2SD2242	I <sub>CEO</sub>	$V_{CE} = 30 \text{ V}, I_B = 0$			500	μΑ
current	2SD2242A	S	$V_{CE} = 40 \text{ V}, I_B = 0$	Ċ.		500	
Emitter cutoff current	CO/V	I <sub>EBO</sub>	$V_{EB} = 5 V, I_C = 0$			2	μΑ
Collector to emitter	2SD2242	V <sub>CEO</sub>	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 0$	60			V
voltage	2SD2242A			80			
Forward current transfe	r ratio	h <sub>FE1</sub>	$V_{CE} = 3 V, I_C = 0.5 A$	1 000			
		h <sub>FE2</sub> *	$V_{CE} = 3 V, I_C = 3 A$	2 000		10 000	
Base to emitter voltage		V <sub>BE</sub>	$V_{CE} = 3 V, I_C = 3 A$			2.5	V
Collector to emitter satu	ration voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 3 \text{ A}, I_{\rm B} = 12 \text{ mA}$			2	V
			$I_{\rm C} = 5 \text{ A}, I_{\rm B} = 20 \text{ mA}$			4	
Transition frequency		f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t <sub>on</sub>	$I_{C} = 3 \text{ A}, I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA},$		0.5		μs
Storage time		t <sub>stg</sub>	$V_{CC} = 50 V$		4		μs
Fall time		t <sub>f</sub>			1		μs

Note) \*: Rank classification

Rank	Q	R

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